

Effects of Top and Bottom Electrodes Materials and Operating Ambiance on the Characteristics of MgF_x Based Bipolar RRAMs

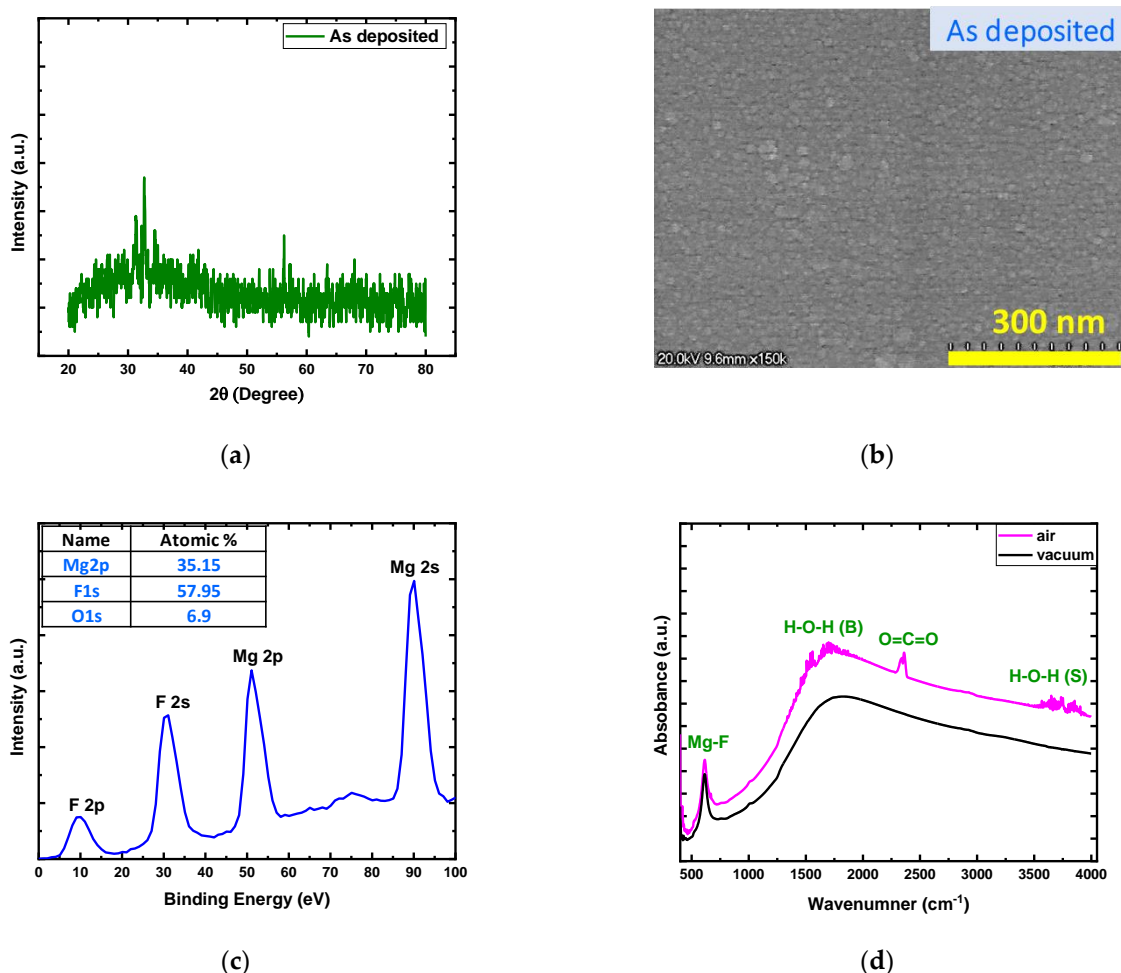


Figure S1. Structural and compositional analysis of MgF_x thin film (a) XRD pattern of MgF_x film; (b) SEM image of the surface; (c) XPS analysis with characteristics peaks and atomic percentages of magnesium and fluorine; (d) FTIR absorbance spectra in open air and vacuum environment [23–25].

References

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